

ABSTRACT OF THE DISCLOSURE

A crystallization method includes forming a black matrix layer that absorbs external light on an insulating substrate, wherein an upper region of the black matrix layer comprises a catalyst for silicon crystallization, patterning the black matrix layer, forming an amorphous silicon thin film on the insulating substrate and the black matrix layer, and thermally processing the amorphous silicon thin film for crystallization. A thin film transistor formed using the crystallization method has improved properties as a continuous metal-induced crystallization region and a metal-induced lateral crystallization region are formed therein without a definite boundary.